

EV372453410

Inventor: Cem Basceri et. al.

Title: Circuit Constructions

Assignee: Micron Technology, Inc.

INFORMATION DISCLOSURE STATEMENT

PURSUANT TO 37 C.F.R. §§1.56, 1.97 AND 1.98

In compliance with 37 C.F.R. §§1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449.

The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a divisional application of U.S. Patent Application Serial No. 10/443,354, which was filed May 21, 2003, which is a continuation-in-part application of U.S. Patent Application Serial No. 10/243,386, filed September 13, 2002; which is a divisional application of U.S. Patent Application Serial No. 09/827,759, filed April 6, 2001 and now U.S. Patent Number 6,511,896. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. §1.98(d) and MPEP §609(2). No admission is made regarding whether all the submitted references are prior art.

Citation of these references is respectfully requested.

Respectfully submitted,

Dated: 3/25/2004

Attorney: 

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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. M22-2515		PRIORITY SERIAL NO. 10443,354	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT Cem Basceri et al.			
					PRIORITY FILING DATE May 21, 2003		PRIORITY GROUP 2518	
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA	5,292,673	03-1994	Shinriki et al.				
	AB	5,486,488	01-1996	Kamiyama				
	AC	5,641,702	06-1997	Imai et al.				
	AD	5,726,083	03-1998	Takaishi				
	AE	5,893,734	04-1999	Jeng et al.				
	AF	6,117,725	09-2000	Huang				
	AG	6,200,893	03-2001	Sneh				
	AH	6,235,572	05-2001	Kunitomo et al.				
	AI	6,399,438	06-2002	Saito et al.				
	AJ	6,511,896	1/28/03	Basceri et al.				
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AK							
	AL							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
	AM		Bin Yu, et al., "70nm MOSFET with Ultra-Shallow, Abrupt, and Super-Doped S/D Extension Implemented by Laser Thermal Process (LTP)", IEEE, 03/1999.					
	AN		Somit Talwar, et al., "Ultra-Shallow, Abrupt, and Highly-Activated Junctions by Low-Energy Ion Implantation and Laser Annealing", Verdant Technologies, San Jose, CA.					
	AO		Ken-ichi Goto, et al., "Ultra-Low Contact Resistance for Deca-nm MOSFETs by Laser Annealing", IEEE, 09/1999, pps. 20.7.1-20.7.3.					
EXAMINER					DATE CONSIDERED			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

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